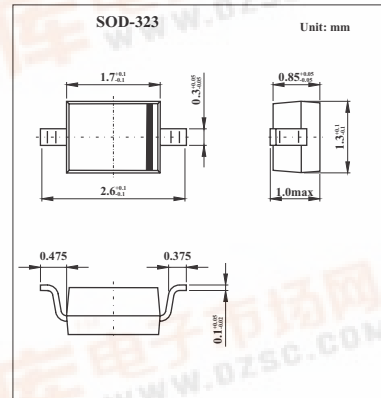


SMD Type Diodes

Silicon Epitaxial Planar Diode
1SV269

Features

- High Capacitance Ratio:C2V/C25V = 11.5(Typ.)
- Low Series Resistance:rs = 0.55 Ω (Typ.)
- Excellent C-V Characteristics,and Small Tracking Error.



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse Voltage	V _R	34	V
Peak Reverse Voltage	V _{RM}	36(R _L = 10 K Ω)	V
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	-55 to +125	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	V _R	I _R = 1 μ A	34			V
Reverse Current	I _R	V _R = 32 V			10	nA
Capacitance	C _{2V}	f = 1 MHz;V _R = 2 V	33	31.5	34	pF
	C _{25V}	f = 1 MHz;V _R = 25 V	2.5	2.75	2.9	
Capacitance Ratio	C _{2V} /C _{25V}		11	11.5		
	C _{25V} /C _{28V}		1.03	1.05		
Series Resistance	r _s	V _R = 5V, f = 470 MHz		0.55	0.7	Ω

Note :

Available in matched group for capacitance to 2.0%.

$$\frac{C(\text{Max.})-C(\text{Min.})}{C(\text{Min.})} \leq 0.020$$

(V_R=2~25V)

Marking

Marking	TE
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